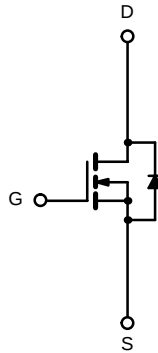
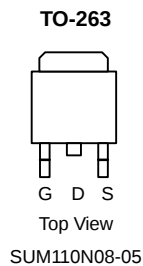




N-Channel 75-V (D-S) 200°C MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
75	0.0048 @ $V_{GS} = 10$ V	110 ^a



N-Channel MOSFET

FEATURES

- TrenchFET® Power MOSFETS
- 200°C Junction Temperature
- New Low Thermal Resistance Package

APPLICATIONS

- Automotive
 - Boardnet 42-V EPS and ABS
 - Motor Drives
- High Current
- DC/DC Converters

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	75	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	I_D	110 ^a	A
	$T_C = 125^\circ\text{C}$		110 ^a	
Pulsed Drain Current		I_{DM}	440	
Avalanche Current		I_{AR}	75	
Repetitive Avalanche Energy ^b	$L = 0.1$ mH	E_{AR}	280	mJ
Maximum Power Dissipation ^b	$T_C = 25^\circ\text{C}$	P_D	437.5 ^c	W
	$T_A = 25^\circ\text{C}^d$		3.7	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 200	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Limit	Unit
Junction-to-Ambient—PCB Mount ^d	R_{thJA}	40	$^\circ\text{C/W}$
Junction-to-Case (Drain	R_{thJC}	0.4	

Notes

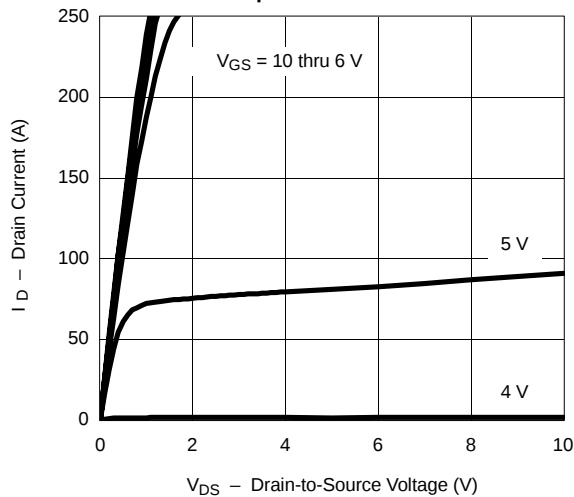
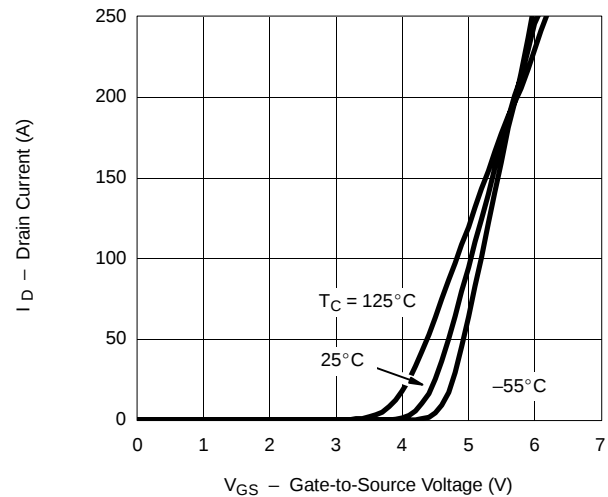
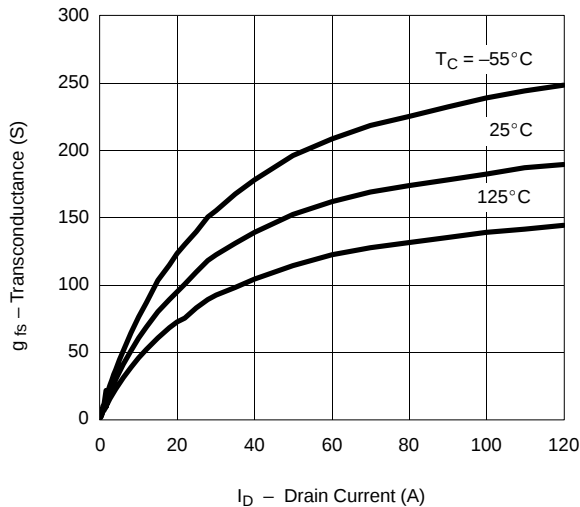
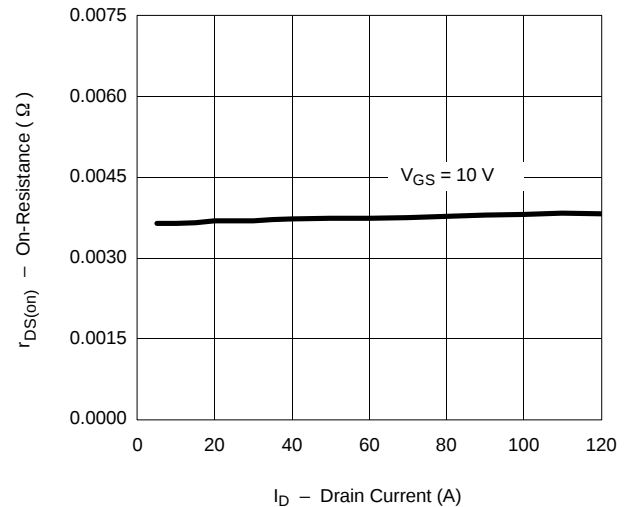
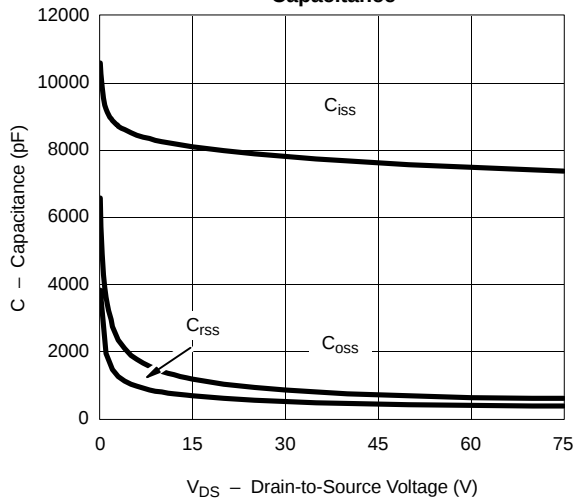
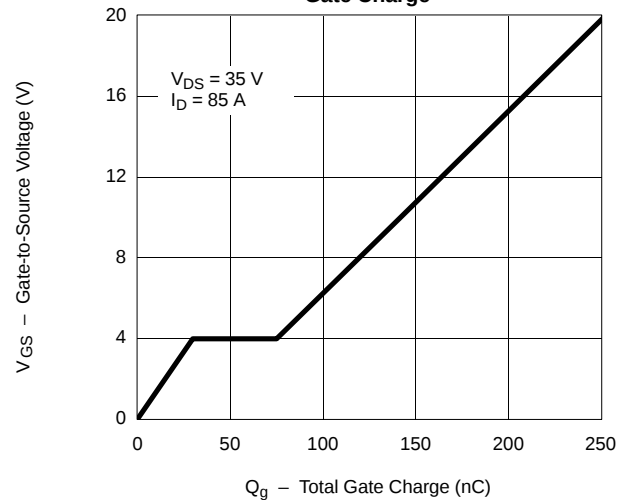
- Package limited.
- Duty cycle $\leq 1\%$.
- See SOA curve for voltage derating.
- When mounted on 1" square PCB (FR-4 material).

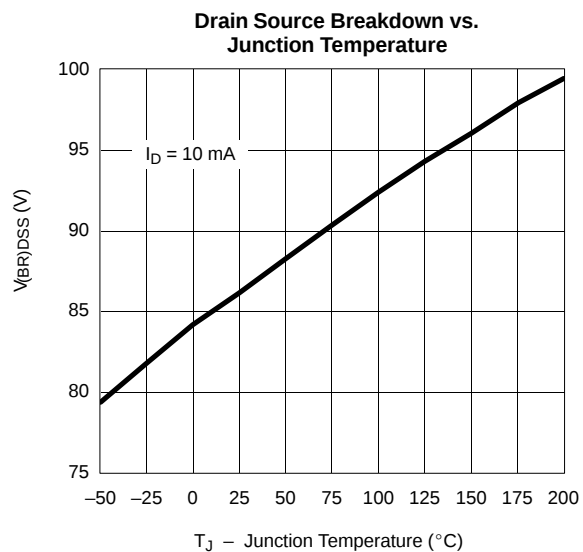
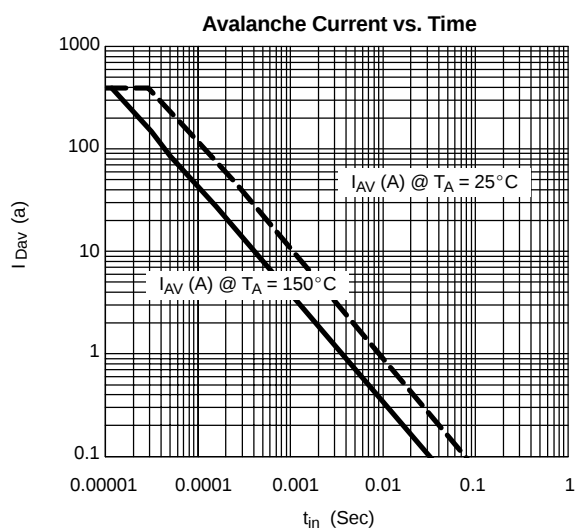
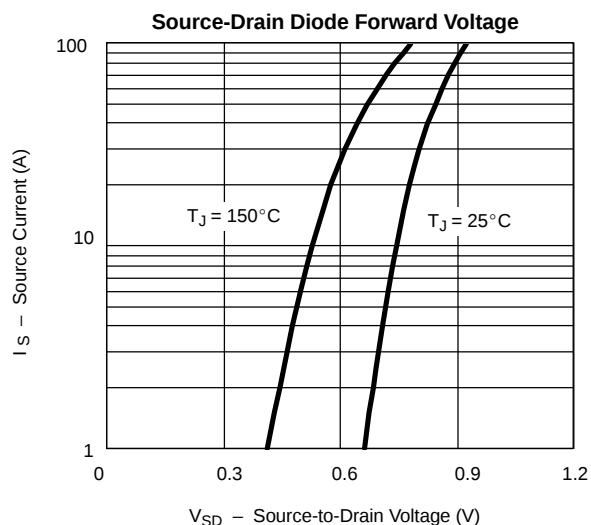
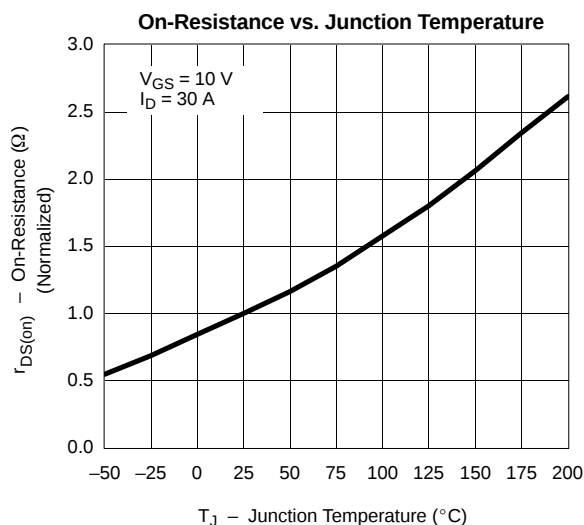
SPECIFICATIONS (T_J = 25 °C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	75			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5			
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125°C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 200°C			10	mA
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.0038	0.0048	Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125°C			0.0084	
		V _{GS} = 10 V, I _D = 30 A, T _J = 200°C			0.00125	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	30			S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		7900		pF
Output Capacitance	C _{oss}			950		
Reverse Transfer Capacitance	C _{rss}			550		
Total Gate Charge ^c	Q _g	V _{DS} = 35 V, V _{GS} = 10 V, I _D = 110 A		145	215	nC
Gate-Source Charge ^c	Q _{gs}			30		
Gate-Drain Charge ^c	Q _{gd}			45		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 35 V, R _L = 0.4 Ω I _D ≅ 110 A, V _{GEN} = 10 V, R _G = 2.5 Ω		25	40	ns
Rise Time ^c	t _r			200	300	
Turn-Off Delay Time ^c	t _{d(off)}			65	100	
Fall Time ^c	t _f			165	250	
Source-Drain Diode Ratings and Characteristics (T _C = 25°C) ^b						
Continuous Current	I _S				110	A
Pulsed Current	I _{SM}				440	
Forward Voltage ^a	V _{SD}	I _F = 110 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 85 A, di/dt = 100 A/μs		80	120	ns
Peak Reverse Recovery Current	I _{RM(REC)}			4	7	A
Reverse Recovery Charge	Q _{rr}			0.16	0.30	μC

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

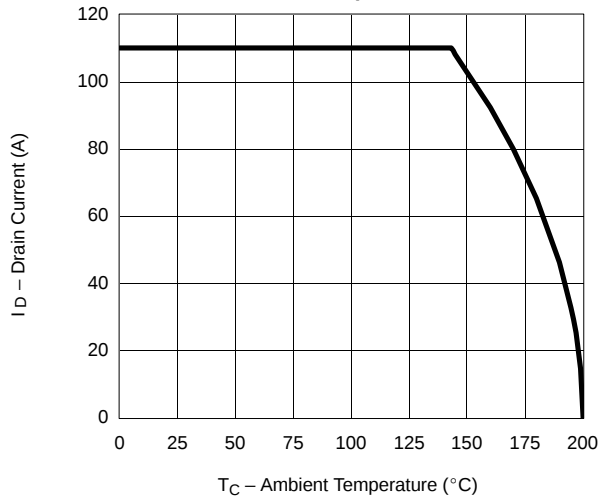
**TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)****Output Characteristics****Transfer Characteristics****Transconductance****On-Resistance vs. Drain Current****Capacitance****Gate Charge**

TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)

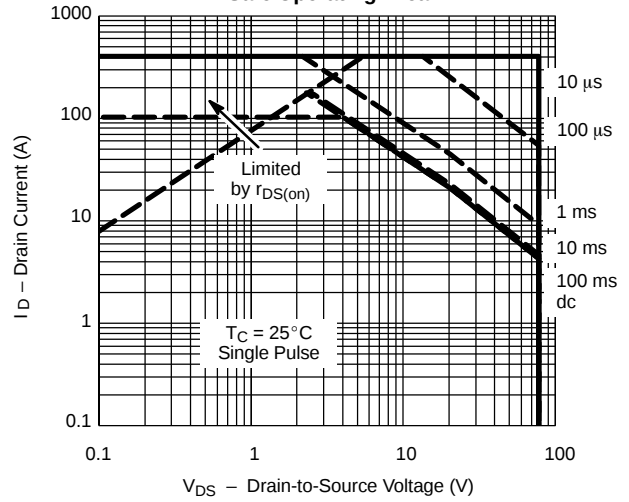


THERMAL RATINGS

Maximum Drain Current vs.
Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

